

## isc Silicon NPN Power Transistor

**BDY29** 

#### **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 75V (Min)
- Low Collector-Emitter Saturation Voltage
- Excellent Safe Operating Area
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

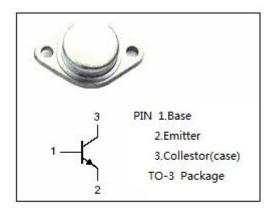
 Designed for use in high power ,high current and switching applications.

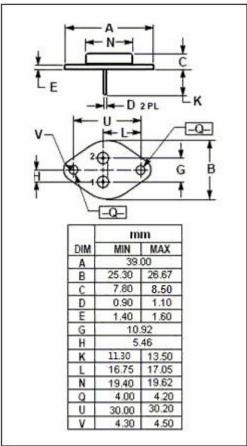
# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

7120020	ABOUTE III BAING (1a 200)							
SYMBOL	PARAMETER	VALUE	UNIT					
$V_{\text{CBO}}$	Collector-Base Voltage	100	V					
V <sub>CEO</sub>	Collector-Emitter Voltage	75	V					
V <sub>EBO</sub>	Emitter-Base Voltage	7	V					
Ic	Collector Current-Continuous	30	Α					
I <sub>B</sub>	Base Current	7.5	Α					
Pc	Collector Power Dissipation @ T <sub>C</sub> =25°C	220	W					
TJ	Junction Temperature	200	$^{\circ}$					
T <sub>stg</sub>	Storage Temperature Range	-65~200	$^{\circ}$					

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	0.8	°C/W







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	75		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 15A; I <sub>B</sub> = 1.5A		1.2	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 30A ; V <sub>CE</sub> = 4V		3.5	V
Icex	Collector Cutoff Current	V <sub>CE</sub> = 100V; V <sub>BE</sub> = -1.5V V <sub>CE</sub> = 100V; V <sub>BE</sub> = -1.5V;T <sub>C</sub> =150℃		1.0 10	mA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 75V; I <sub>B</sub> = 0		2.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0		1.0	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 15A ; V <sub>CE</sub> = 2V	15	60	
I <sub>s/b</sub>	Second Breakdown Collector Current with Base Forward Biased	V <sub>CE</sub> = 60V,t= 1.0s,Nonrepetitive	3.66		А
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V	4		MHz

### **NOTICE:**

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